PROCESS CPD73

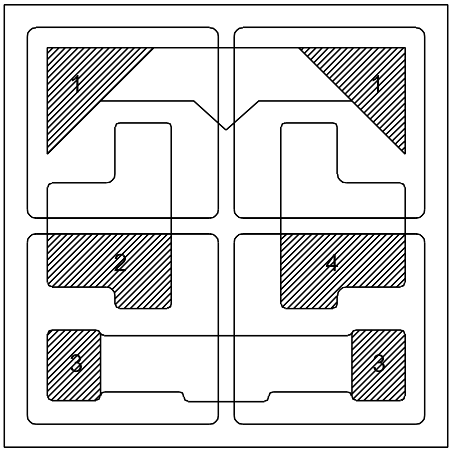
Bridge Rectifier

Monolithic Quad Diode Bridge Chip

PROCESS DETAILS

Die Size	25 x 25 MILS
Die Thickness	6.0 MILS
Bonding Pad Area 1 (+DC)	3.0 x 3.0 MILS
Bonding Pad Area 2 (AC)	3.0 x 7.0 MILS
Bonding Pad Area 3 (-DC)	3.0 x 4.0 MILS
Bonding Pad Area 4 (AC)	3.0 x 7.0 MILS
Top Side Metalization	Al - 12,000Å
Back Side Metalization	Au - 5,000Å

GEOMETRY



R1

GROSS DIE PER 3 INCH WAFER
10,000

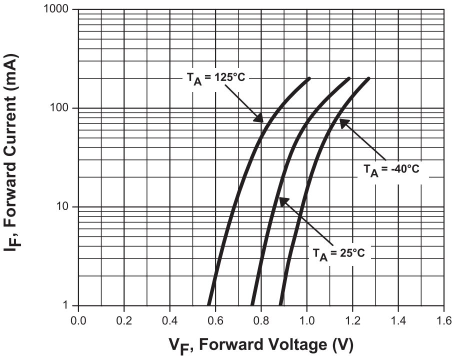
PRINCIPAL DEVICE TYPES
CMFBR-6F

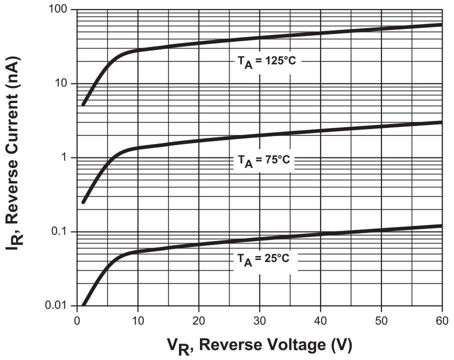
R2 (22-March 2010)

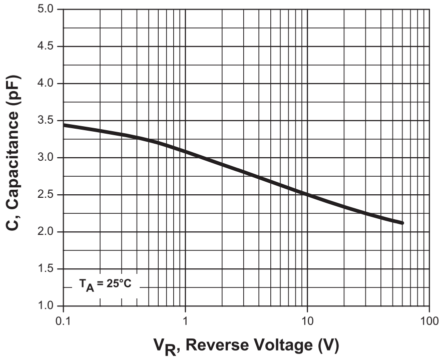
PROCESS CPD73

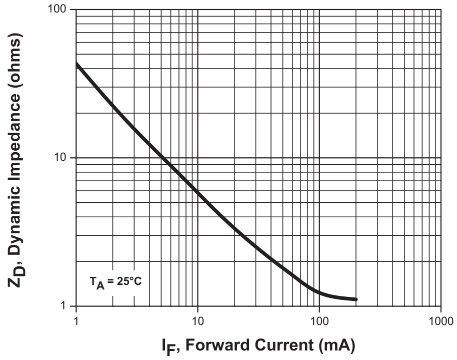
Typical Electrical Characteristics

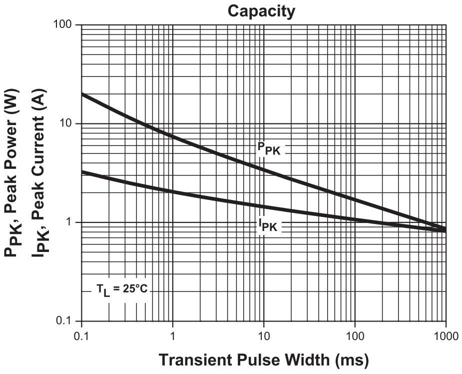
Central Semiconductor Corp.

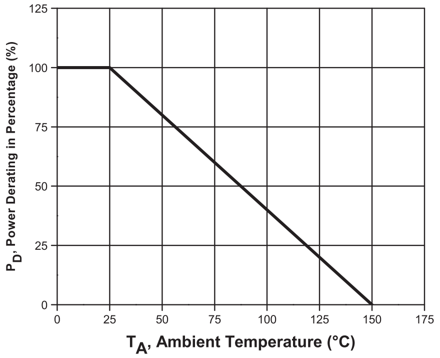

Forward Voltage


Leakage Current


Capacitance


Forward Dynamic Impedance


Transient Peak Power and Peak Current Capacity


Normalized Power Derating